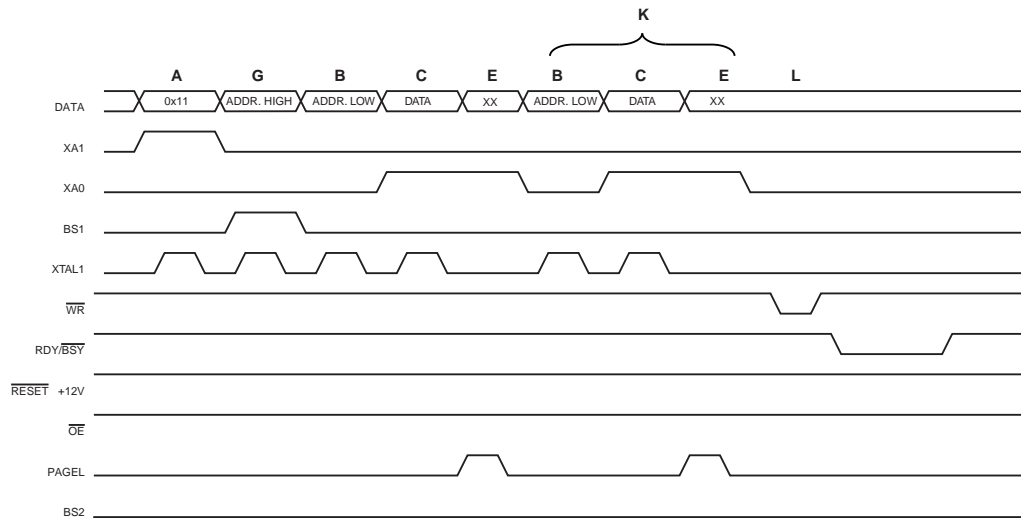


5. E: Latch data (give $\overline{\text{PAGEL}}$ a positive pulse).
 - K: Repeat 3 through 5 until the entire buffer is filled.
 - L: Program EEPROM page
1. Set BS1 to “0”.
 2. Give $\overline{\text{WR}}$ a negative pulse. This starts programming of the EEPROM page. RDY/ $\overline{\text{BSY}}$ goes low.
 3. Wait until RDY/ $\overline{\text{BSY}}$ goes high before programming the next page (See [Figure 25-4](#) for signal waveforms).

Figure 25-4. Programming the EEPROM Waveforms



25.7.6 Reading the Flash

The algorithm for reading the Flash memory is as follows (refer to ["Programming the Flash"](#) on [page 302](#) for details on Command and Address loading):

1. A: Load Command "0000 0010".
2. G: Load Address High Byte (0x00 - 0xFF).
3. B: Load Address Low Byte (0x00 - 0xFF).
4. Set $\overline{\text{OE}}$ to "0", and BS1 to "0". The Flash word low byte can now be read at DATA.
5. Set BS1 to "1". The Flash word high byte can now be read at DATA.
6. Set $\overline{\text{OE}}$ to "1".

25.7.7 Reading the EEPROM

The algorithm for reading the EEPROM memory is as follows (refer to ["Programming the Flash"](#) on [page 302](#) for details on Command and Address loading):

1. A: Load Command "0000 0011".
2. G: Load Address High Byte (0x00 - 0xFF).
3. B: Load Address Low Byte (0x00 - 0xFF).
4. Set $\overline{\text{OE}}$ to "0", and BS1 to "0". The EEPROM Data byte can now be read at DATA.
5. Set $\overline{\text{OE}}$ to "1".